November 2012



# FGA25S125P Shorted Anode™ IGBT

## Features

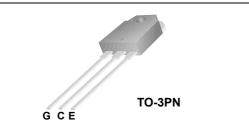
- · High speed switching
- Low saturation voltage: V<sub>CE(sat)</sub> =1.8V @ I<sub>C</sub> = 25A
- High input impedance
- RoHS compliant

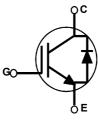
# Applications

- Induction Heating and Microwave Oven
- Soft Switching Applications

## **General Description**

Using advanced Field Stop Trench and Shorted Anode technology, Fairchild's Shorted Anode<sup>TM</sup> Trench IGBTs offer superior conduction and switching performances, and easy parallel operation with exceptional avalanche capability. This device is desingned for induction heating and microwave oven.





## **Absolute Maximum Ratings**

Symbol	Description		Rating	Units
V <sub>CES</sub>	Collector to Emitter Voltage		1250	V
V <sub>GES</sub>	Gate to Emitter Voltage		± 25	V
1.	Collector Current	@ T <sub>C</sub> = 25°C	50	A
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 100°C	25	А
I <sub>CM (1)</sub>	Pulsed Collector Current		75	A
l <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 25°C	50	А
۰F	Diode Continuous Forward Current	@ T <sub>C</sub> = 100 <sup>o</sup> C	25	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	250	W
١D	Maximum Power Dissipation	@ T <sub>C</sub> = 100 <sup>o</sup> C	125	W
TJ	Operating Junction Temperature		-55 to +175	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

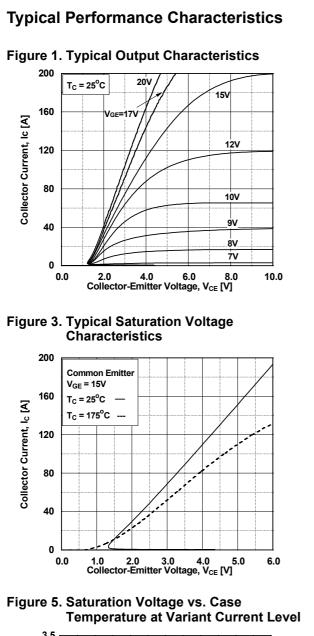
## **Thermal Characteristics**

Symbol	Symbol Parameter		Max.	Units
$R_{\theta JC}$ (IGBT)	(IGBT) Thermal Resistance, Junction to Case, Max		0.6	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient, Max	-	40	°C/W

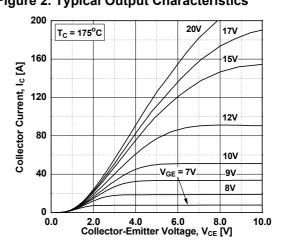
Notes:

1: Limited by Tjmax

Device N	larking	Device	Package	Reel Size	Таре	Width	Qua	antity
FGA25S125P FGA25S125P 1		TO-3PN	го-зрn -		-		30	
Electric	al Chara	acteristics of	the IGBT т	c = 25°C unless otherwise noted				
Symbol		Parameter	Т	est Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics							
I <sub>CES</sub>	Collector C	Cut-Off Current	V <sub>CE</sub> = 12	250V, V <sub>GE</sub> = 0V	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current			<sub>GES</sub> , V <sub>CE</sub> = 0V	-	-	±500	nA
On Change	to viation		ł			1		
On Charac		hold Voltago	L. = 25n	$\lambda = - \lambda = -$	4.5	6.0	7.5	V
V <sub>GE(th)</sub>		hold Voltage		nA, V <sub>CE</sub> = V <sub>GE</sub> , V <sub>GE</sub> = 15V	4.0	0.0	-	v
	Collector to Emitter Saturation Voltage		$T_{\rm C} = 25^{\circ}$	C	-	1.8	2.35	V
V <sub>CE(sat)</sub>			oltage $I_C = 25A$ $T_C = 125$	, V <sub>GE</sub> = 15V 5°C	-	2.05	-	V
			I <sub>C</sub> = 25A T <sub>C</sub> = 175	, V <sub>GE</sub> = 15V, 5°C	-	2.16	-	V
. ,	Diode Forward Voltage		I <sub>F</sub> = 25A	, T <sub>C</sub> = 25°C	-	1.7	2.4	V
V <sub>FM</sub>			I <sub>F</sub> = 25A	, T <sub>C</sub> = 175 <sup>o</sup> C	-	2.1	-	V
Dvnamic C	haracterist	ics						
C <sub>ies</sub>	Input Capa				-	2150	-	pF
C <sub>oes</sub>	Output Ca	pacitance		$V_{\rm V}$ V <sub>GE</sub> = 0V,	-	48	-	pF
C <sub>res</sub>	Reverse Tr	Reverse Transfer Capacitance		f = 1MHz		36	-	pF
Switching	Characteris	tics	·					
t <sub>d(on)</sub>	Turn-On D				_	24	_	ns
t <sub>r</sub>	Rise Time				-	250	-	ns
t <sub>d(off)</sub>	Turn-Off D	elay Time	V = 6			502	-	ns
t <sub>f</sub>	Fall Time		R <sub>G</sub> = 10	Ω, V <sub>GE</sub> = 15V,	-	138	179	ns
E <sub>on</sub>	Turn-On S	witching Loss	Resistiv	e Load, T <sub>C</sub> = 25ºC	-	1085	-	uJ
E <sub>off</sub>	Turn-Off S	witching Loss			-	580	754	uJ
E <sub>ts</sub>	Total Switc	hing Loss		1		1665	-	uJ
t <sub>d(on)</sub>	Turn-On D	elay Time			-	21.2	-	ns
t <sub>r</sub>	Rise Time				-	304	-	ns
t <sub>d(off)</sub>	Turn-Off D	elay Time		00V, I <sub>C</sub> = 25A,	-	490	-	ns
t <sub>f</sub>	Fall Time			$Ω, V_{GE} = 15V,$	-	232	-	ns
E <sub>on</sub>	Turn-On S	witching Loss	Kesistiv	e Load,, T <sub>C</sub> = 175 <sup>o</sup> C	-	1310	-	uJ
E <sub>off</sub>	Turn-Off S	witching Loss			-	952	-	uJ
E <sub>ts</sub>	Total Switc	hing Loss			-	2262	-	uJ
Qg	Total Gate	Charge			-	204	-	nC
Q <sub>ge</sub>	Gate to En	nitter Charge	V <sub>CE</sub> = 60 V <sub>GE</sub> = 1	00V, I <sub>C</sub> = 25A, 5V	-	15	-	nC
Q <sub>gc</sub>	Gate to Co	llector Charge	GE - I	· ·	-	103	-	nC



# Figure 2. Typical Output Characteristics



**Figure 4. Transfer Characteristics** 

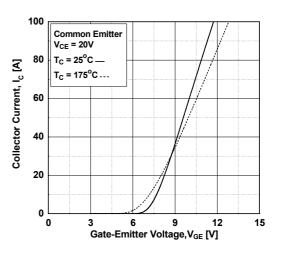
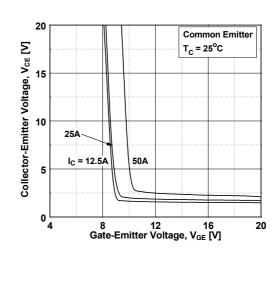
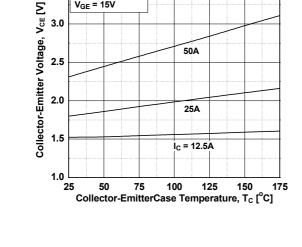
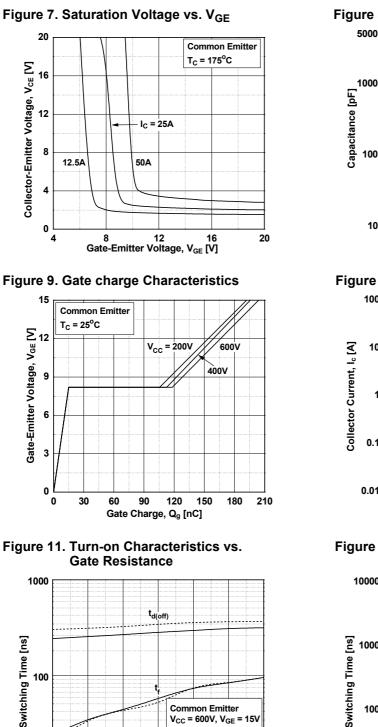


Figure 6. Saturation Voltage vs. V<sub>GE</sub>







Common Emitter

I<sub>C</sub> = 25A

T<sub>C</sub> = 25<sup>o</sup>C

T<sub>C</sub> = 175°C ---

50

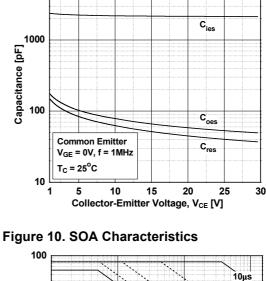
V<sub>CC</sub> = 600V, V<sub>GE</sub> = 15V

60

70

**Typical Performance Characteristics** 

**Figure 8. Capacitance Characteristics** 



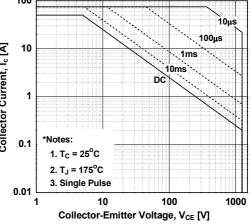
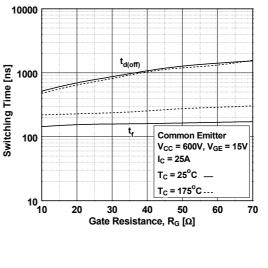


Figure 12. Turn-off Characteristics vs. **Gate Resistance** 



100

10 └ 10

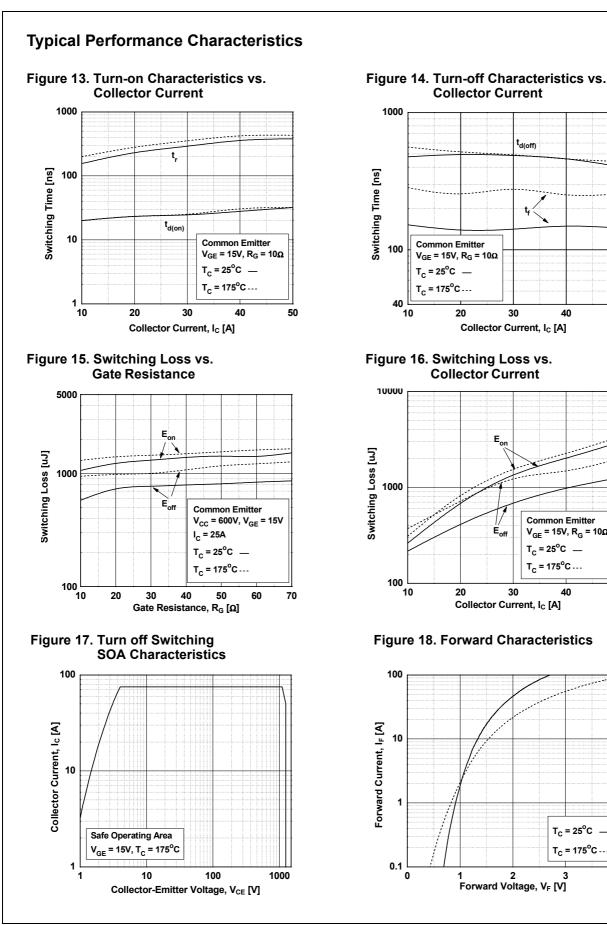
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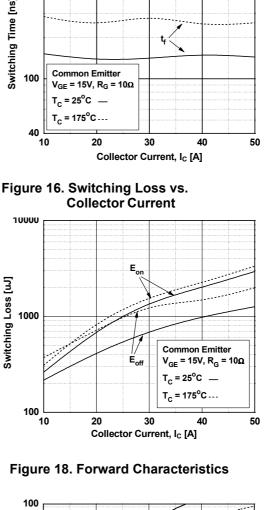
30

40

Gate Resistance,  $R_G [\Omega]$ 

FGA25S125P Shorted Anode<sup>TM</sup> IGBT

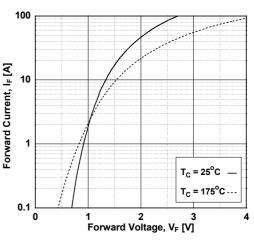




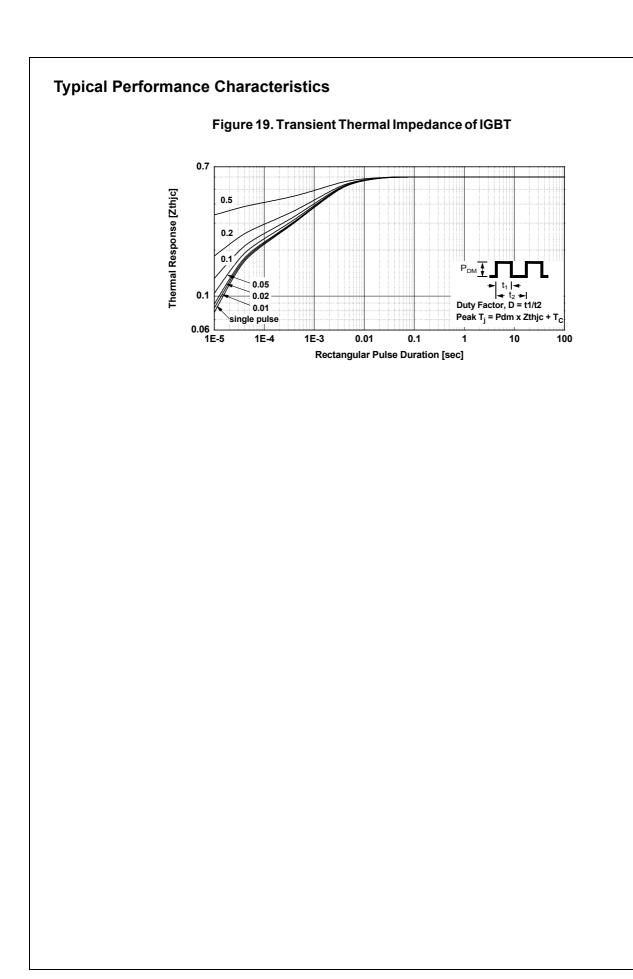
**Collector Current** 

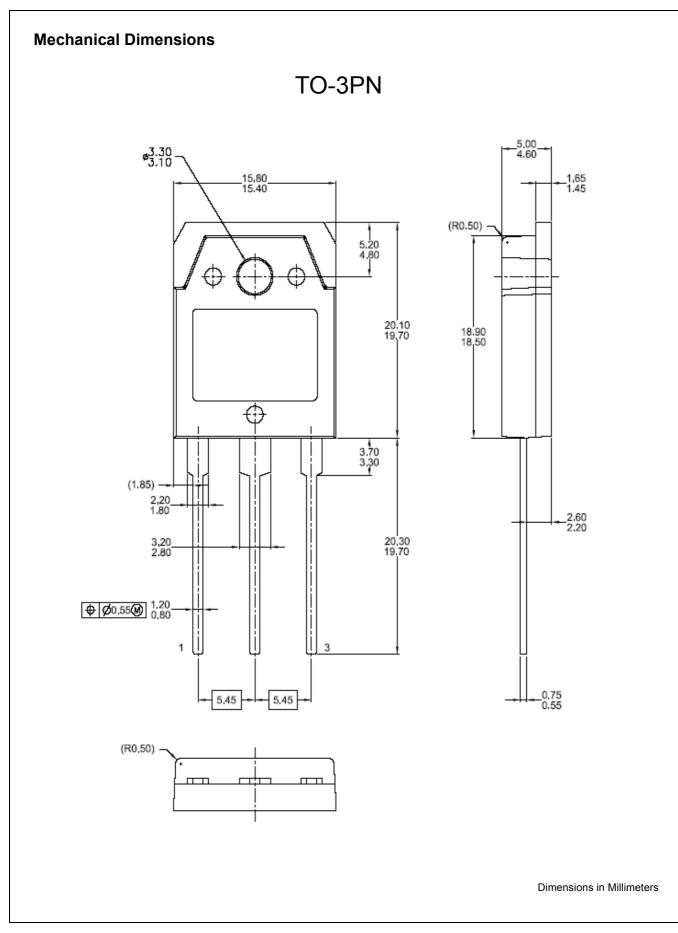
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t<sub>d(off)</sub>



FGA25S125P Rev. C0







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